

1SS355

100mA Surface Mount Small Signal Switching Diode-90V

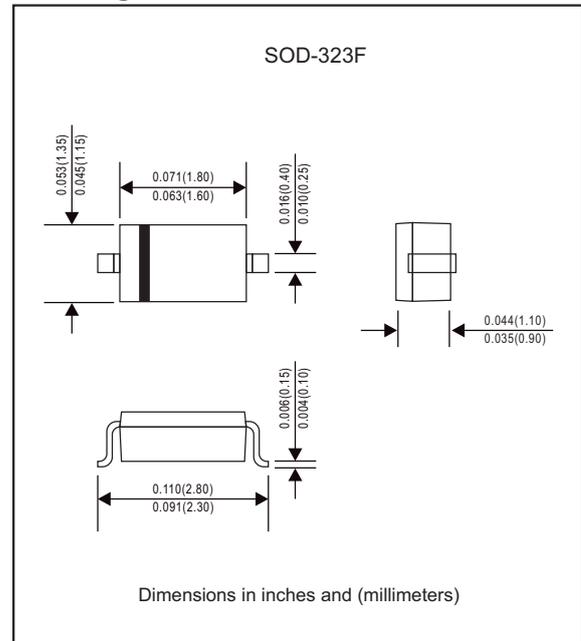
Features

- Small surface mounting type
- High speed
- High reliability with high surge current handling capability
- We declare that the material of product compliance with RoHS requirements
- Silicon epitaxial planar chip, metal silicon junction
- Lead-free parts meet RoHS requirements
- Suffix "-H" for Halogen-free part, ex. 1SS355-H

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, SOD-323F
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.005 gram

Package Outline



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_O	100	mA
Surge current (1s)	I_{surge}	500	mA
Operating junction temperature range	T_J	-55 to +150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Forward voltage($I_F=100\text{mA}$)	V_F			1.2	V
Reverse voltage leakage current($V_R=80\text{Vdc}$)	I_R			0.1	μA
Diode capacitance($V_R=0.5\text{V}$, $f=1.0\text{MHz}$)	C_T			3.0	pF
Reverse recover time($V_R=6\text{V}$, $I_F=10\text{mA}$, $R_L=100\Omega$)	t_{rr}			4.0	ns

Thermal characteristics

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Total device dissipation FR-5 Board*1, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D			225	mW
Thermal resistance junction to ambient	$R_{\theta JA}$			1.8	$\text{mW}/^\circ\text{C}$
Total device dissipation alumina Substrate*2, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D			300	mW
Thermal resistance junction to ambient	$R_{\theta JA}$			2.4	$\text{mW}/^\circ\text{C}$
				417	$^\circ\text{C}/\text{W}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

Rating and characteristic curves (1SS355)

Fig.1 Forward characteristics

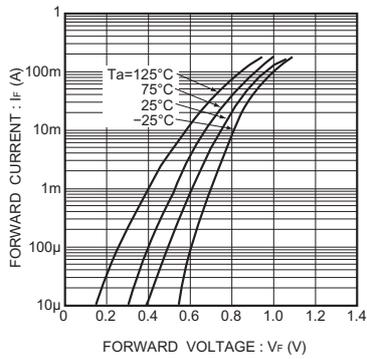


Fig.2 Reverse characteristics

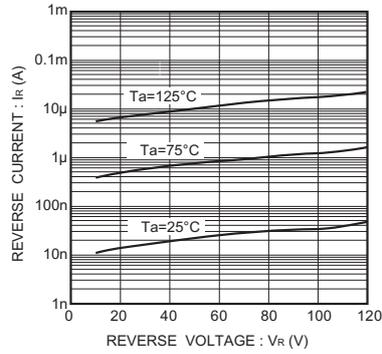


Fig.3 Capacitance between terminals characteristics

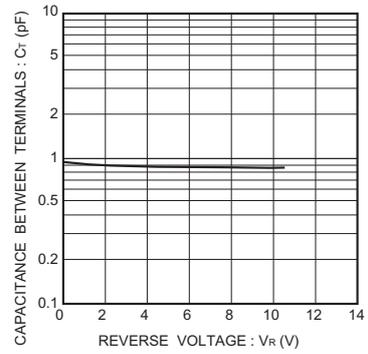


Fig.4 Reverse recovery time characteristics

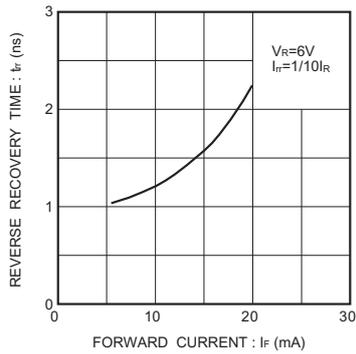


Fig.5 Surge current characteristics

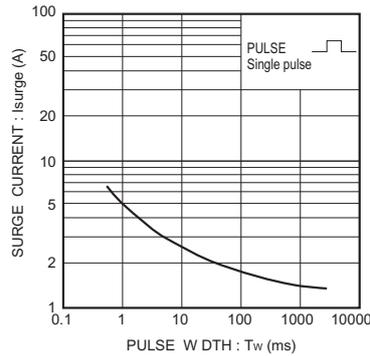
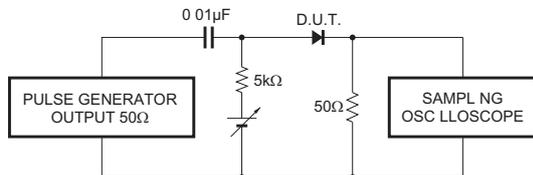


Fig.6 Reverse recovery time (t_{rr}) measurement circuit



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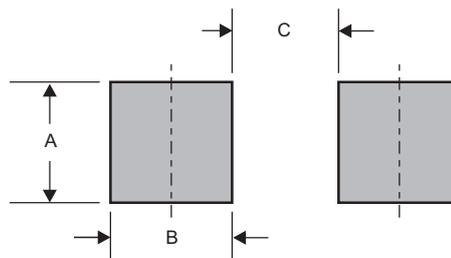
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
1SS355	5D,T4

Suggested solder pad layout

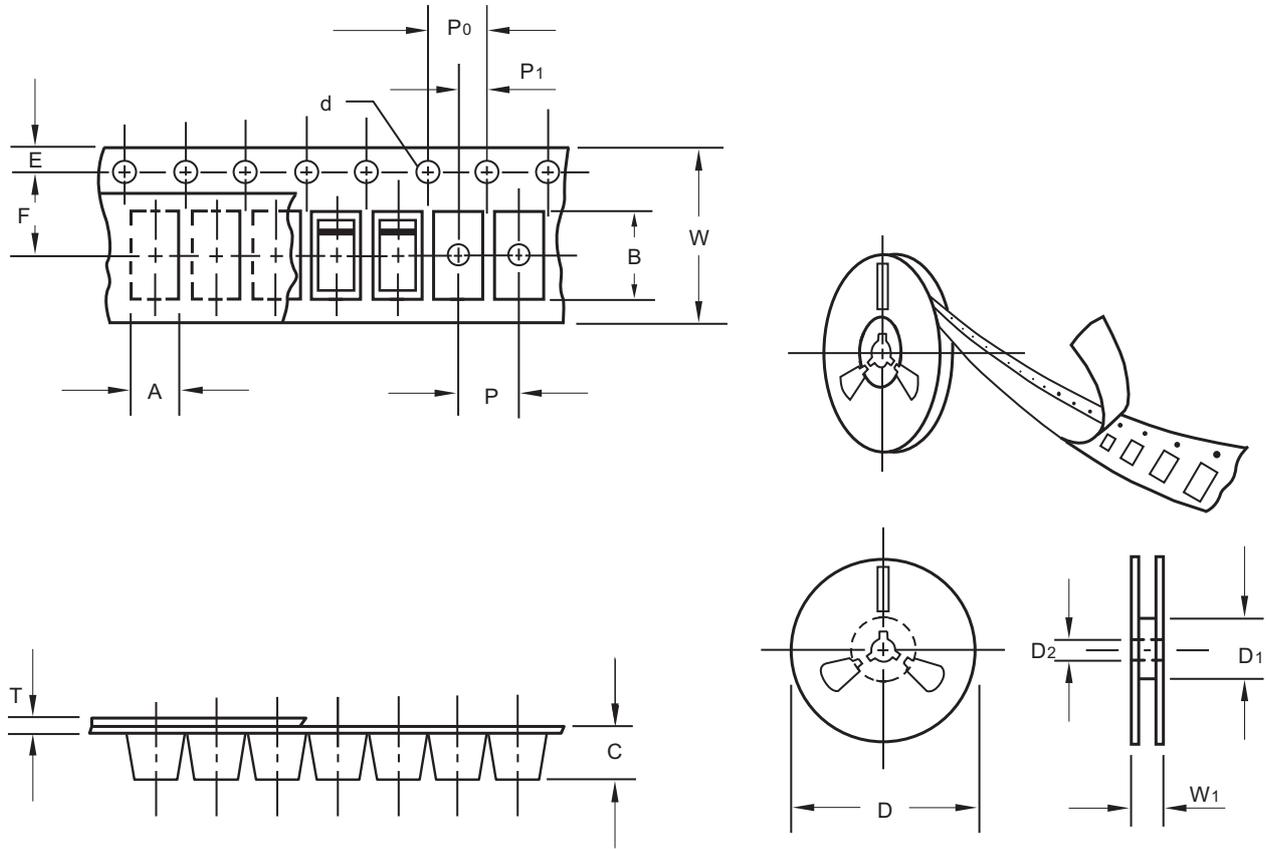


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SOD-323F	0.033 (0.83)	0.025 (0.63)	0.063 (1.60)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOD-323F
Carrier width	A	0.1	1.46
Carrier length	B	0.1	2.95
Carrier depth	C	0.1	1.25
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

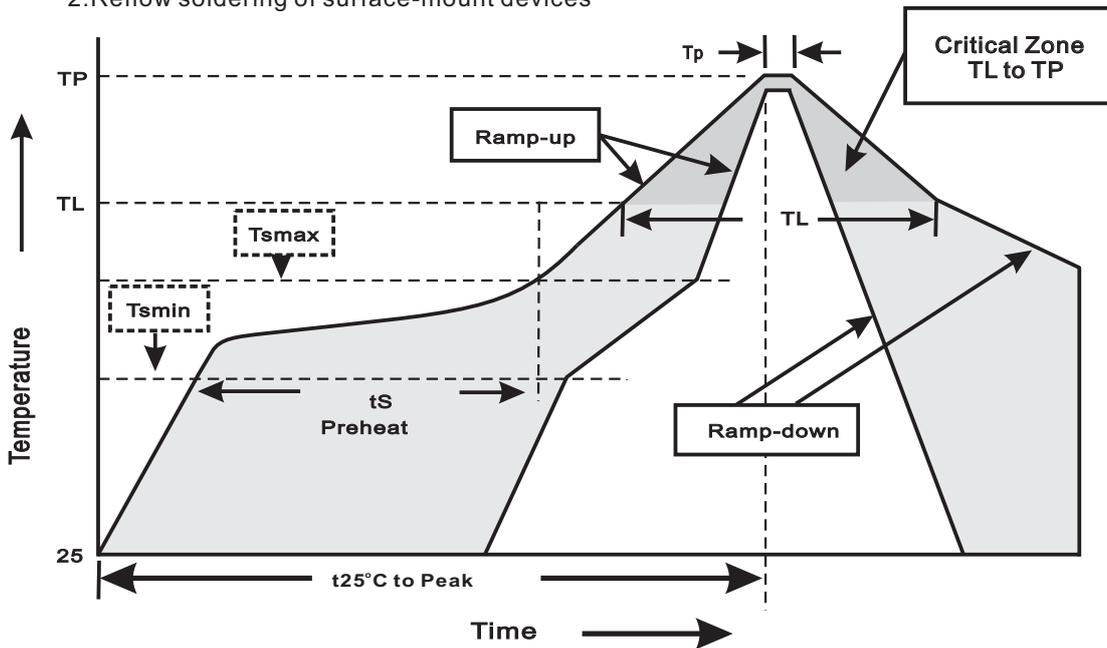
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOD-323F	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	8.0

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smín}) -Temperature Max(T _{smáx}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smáx} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec.	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^\circ\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^\circ\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	15P _{SIG} at $T_A=121^\circ\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Surge Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 150°C for 1000 hrs.	MIL-STD-750D METHOD-1031